

IMD14

Transistors

IMD14 General purpose (dual digital transistors)

IMD14

• Features

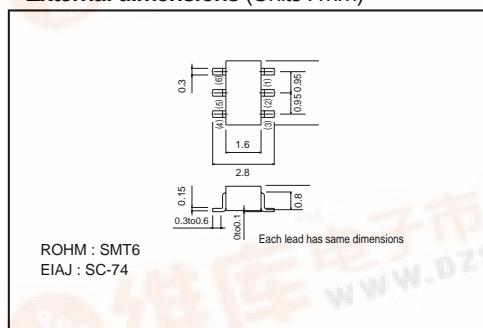
- 1) Two 500 mA digital transistor chips in a SMT package.
 - 2) The drive transistors are independent, eliminating interference.

● Absolute maximum ratings ($T_A = 25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
Supply voltage	V _{CC}	50	V
Input voltage	V _{IN}	5	V
		-5	
Output current	I _C	500	mA
Power dissipation	P _D	300 (TOTAL)	mW *
Junction temperature	T _J	150	°C
Storage temperature	T _{STG}	-55+150	°C

* 200mW per element must not be exceeded. PNP type negative symbols have been omitted.

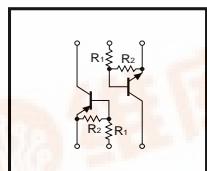
●External dimensions (Units : mm)



● Packaging specifications and h_{FE}

Part No.	IMD14
Package	SMT6
Marking	D14
Code	T108
Basic ordering unit (pieces)	3000

● Circuit diagram



● Electrical characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Input voltage	V _I (off)	—	—	0.3	V	V _{CC} =5V , I _O =100μA
	V _I (on)	1.1	—	—		V _O =0.3V , I _O =1mA
Output voltage	V _O (on)	—	—	0.3	V	I _O /I _L =100mA/5mA
Input current	I _I	—	—	17	mA	V _I =3V
Output current	I _O (off)	—	—	0.5	μA	V _{CC} =50V , V _I =0V
DC current gain	G _H *1	82	—	—	—	I _O =100mA , V _O =5V
Transition frequency	f _T *2	—	250	—	MHz	V _{CE} =10V , I _E =-50mA , f=100MHz
Input resistance	R _I	154	220	286	Ω	—
Resistance ratio	R _Z /R _I	36.3	45.5	54.6	—	—

*1 Measured using pulse current *2 Transition frequency of the device
PNP type negative symbols have been omitted.